TOSHIBA

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HCT08AP, TC74HCT08AF, TC74HCT08AFN

QUAD 2-INPUT AND GATE

The TC74HCT08A is a high speed CMOS 2-INPUT AND GATE fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are

TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

The internal circuit is composed of 4-stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

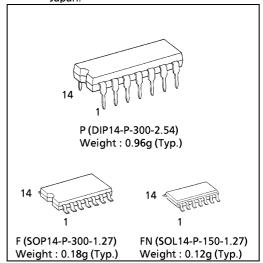
FEATURES:

- High Speed-----t_{pd} = 10ns(typ.) at V_{CC} = 5V
- Low Power Dissipation ············ $I_{CC} = 1 \mu A(Max.)$ at Ta = 25°C
- Compatible with TTL outputs.....V_{IH} = 2V (Min.)

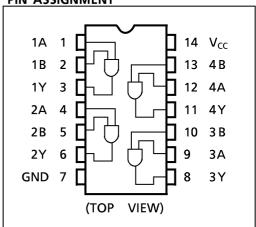
 $V_{IL} = 0.8V (Max.)$

- Wide interfacing ability LSTTL, NMOS, CMOS
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance··· | I_{OH} | = I_{OL} = 4mA(Min.)
- Balanced Propagation Delays ····· t_{pLH} ≃ t_{pHL}
- Pin and Function Compatible with 74LS08

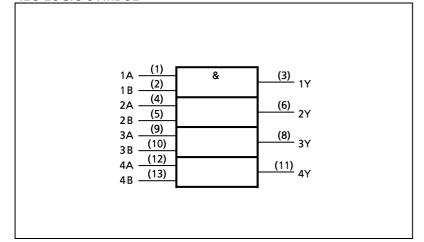
(Note) The JEDEC SOP (FN) is not available in Japan.



PIN ASSIGNMENT



IEC LOGIC SYMBOL TRUT



TRUTH TABLE

Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

961001EBA2

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{cc}	−0.5~7	V
DC Input Voltage	VIN	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V _{OUT}	−0.5~V _{CC} + 0.5	V
Input Diode Current	I _{LK}	± 20	mA
Output Diode Current	I _{OK}	± 20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} / Ground Current	I _{CC}	± 50	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T _{stg}	−65~150	°C

^{*500}mW in the range of Ta= $-40^{\circ}\text{C}\sim65^{\circ}\text{C}$. From Ta=65°C to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{cc}	4.5~5.5	٧
Input Voltage	V _{IN}	0~V _{cc}	V
Output Voltage	V _{OUT}	0∼V _{cc}	V
Operating Temperature	T _{opr}	−40~85	°C
Input Rise and Fall Time	t _r , t _f	0~500	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBO		TEST CONDITION		V _{cc}	٦	Ta = 25°C		Ta = − 40~85°C		UNIT
				(V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
High - Level Input Voltage	V _{IH}			4.5 \$ 5.5	2.0	_	_	2.0	_	>
Low - Level Input Voltage	VIL			4.5 5.5	1	_	0.8	_	0.8	<
High - Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	\ \	
		$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	"	
Low - Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 20 \mu A$	4.5	ı	0.0	0.1	_	0.1	V
Output Voltage	VOL		$I_{OL} = 4 \text{ mA}$	4.5	_	0.17	0.26	_	0.33	
Input Leakage Current	I _{I N}	$V_{IN} = V_{CC}$ or GND		5.5	_	_	± 0.1	_	± 1.0	_
		$V_{1N} = V_{C}$	c or GND	5.5	1	_	1.0	_	10.0	μ A
Quiescent Supply Current	l _c	PER INPUT:V _{IN} OTHER INPUT	_N = 0.5V or 2.4V :V _{CC} or GND	5.5		_	2.0	_	2.9	mA

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, $Ta = 25^{\circ}C$, Input $t_r = t_f = 6ns$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t _{TLH} t _{THL}		_	6	12	
Propagation Delay Time	t _{pLH} t _{pHL}		_	10	16	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = −40~85°C		UNIT
			$V_{CC}(V)$	MIN.	TYP.	MAX.	MIN.	MAX.	CIVII
Output Transition Time	t _{TLH}		4.5	_	8	15	_	19	
	t _{THL}		5.5	_	7	13	_	16	ns
Propagation Delay Time	t _{pLH}		4.5	_	13	20	_	25	
	t _{pHL}		5.5	_	11	18	_	23	
Input Capacitance	C _{IN}				5	10	_	10	рF
Power Dissipation Capacitance	C _{PD} (1)				24	_	_	_	рΓ

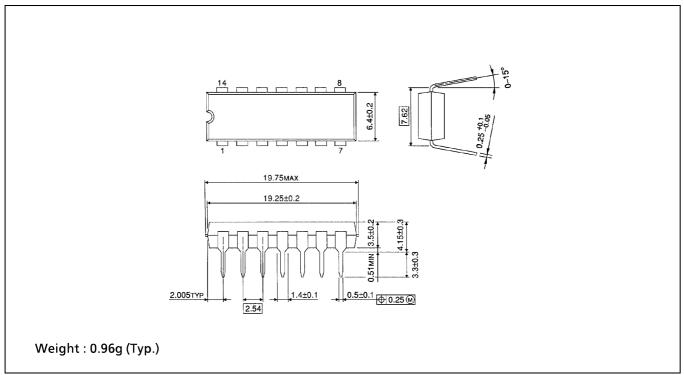
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4$ (per Gate)

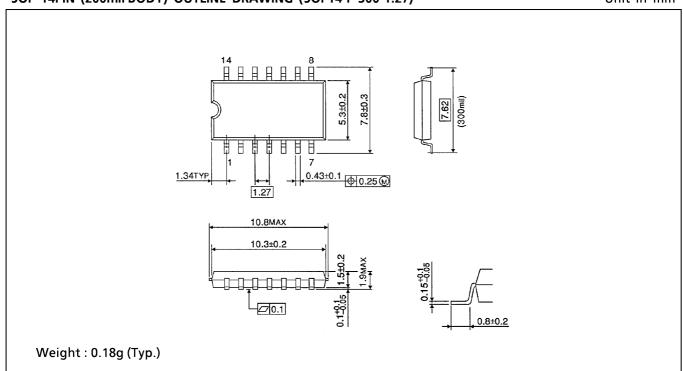
DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)

Unit in mm

